

ABSTRACT OF THE DISCLOSURE

A gate electrode is formed of a laminate structure comprising a plurality of conductive layers such that the width along the channel of a lower first conductive layer is larger than that of an upper second conductive layer. The gate electrode is used as a mask
5 during ion doping for forming an LDD. A mask pattern for forming the gate electrode is processed into an optimum shape in combination with dry etching so that the LDD overlapping with the gate electrode(Lov) is 1 μm or more, and preferably, 1.5 μm or more.